

RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

Designed for broadband commercial and industrial applications with frequencies from 400 to 500 MHz. The high gain and broadband performance of these devices make them ideal for large-signal, common-source amplifier applications in 28-volt base station equipment.

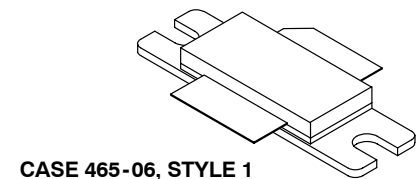
- Typical Single-Carrier N-CDMA Performance @ 465 MHz: $V_{DD} = 28$ Volts, $I_{DQ} = 1250$ mA, $P_{out} = 28$ Watts Avg., IS-95 CDMA (Pilot, Sync, Paging, Traffic Codes 8 Through 13). Channel Bandwidth = 1.2288 MHz. PAR = 9.8 dB @ 0.01% Probability on CCDF.
Power Gain — 21 dB
Drain Efficiency — 30%
ACPR @ 750 kHz Offset — -47.6 dBc in 30 kHz Bandwidth
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 465 MHz, 140 Watts CW Output Power

Features

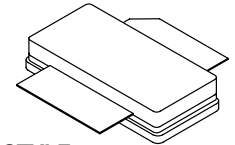
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified Up to a Maximum of 32 V_{DD} Operation
- Integrated ESD Protection
- Lower Thermal Resistance Package
- Low Gold Plating Thickness on Leads, 40 μ m Nominal.
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

MRF5S4140HR3
MRF5S4140HSR3

465 MHz, 28 W AVG., 28 V
SINGLE N-CDMA
LATERAL N-CHANNEL
RF POWER MOSFETs



CASE 465-06, STYLE 1
NI-780
MRF5S4140HR3



CASE 465A-06, STYLE 1
NI-780S
MRF5S4140HSR3

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +65	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +15	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	427 2.4	W W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to +150	$^\circ\text{C}$
Case Operating Temperature	T_C	150	$^\circ\text{C}$
Operating Junction Temperature	T_J	200	$^\circ\text{C}$

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (1,2)	Unit
Thermal Resistance, Junction to Case Case Temperature 73°C , 140 W CW Case Temperature 74°C , 28 W CW	$R_{\theta JC}$	0.41 0.47	$^\circ\text{C}/\text{W}$

1. MTTF calculator available at <http://www.freescale.com/rf>. Select Tools/Software/Application Software/Calculators to access the MTTF calculators by product.
2. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	2 (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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Off Characteristics

Zero Gate Voltage Drain Leakage Current ($V_{DS} = 65\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc

On Characteristics

Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 400\text{ }\mu\text{Adc}$)	$V_{GS(th)}$	2	3	4	Vdc
Gate Quiescent Voltage ($V_{DS} = 28\text{ Vdc}$, $I_D = 1250\text{ mAdc}$, Measured in Functional Test)	$V_{GS(Q)}$	3	4	5	Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 2.42\text{ Adc}$)	$V_{DS(on)}$	0.1	0.2	0.3	Vdc
Forward Transconductance ($V_{DS} = 10\text{ Vdc}$, $I_D = 3\text{ Adc}$)	g_{fs}	—	6.2	—	S

Dynamic Characteristics ⁽¹⁾

Reverse Transfer Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{rss}	—	2.3	—	pF
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Functional Tests (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 1250\text{ mA}$, $P_{out} = 28\text{ W Avg. N-CDMA}$, $f = 465\text{ MHz}$, Single-Carrier N-CDMA, 1.2288 MHz Channel Bandwidth Carrier. ACPR measured in 30 kHz Channel Bandwidth @ $\pm 750\text{ kHz}$ Offset. PAR = 9.8 dB @ 0.01% Probability on CCDF.

Power Gain	G_{ps}	20	21	23	dB
Drain Efficiency	η_D	28.5	30	—	%
Adjacent Channel Power Ratio	ACPR	—	-47.6	-45	dBc
Input Return Loss	IRL	—	-14	-9	dB

1. Part internally input matched.

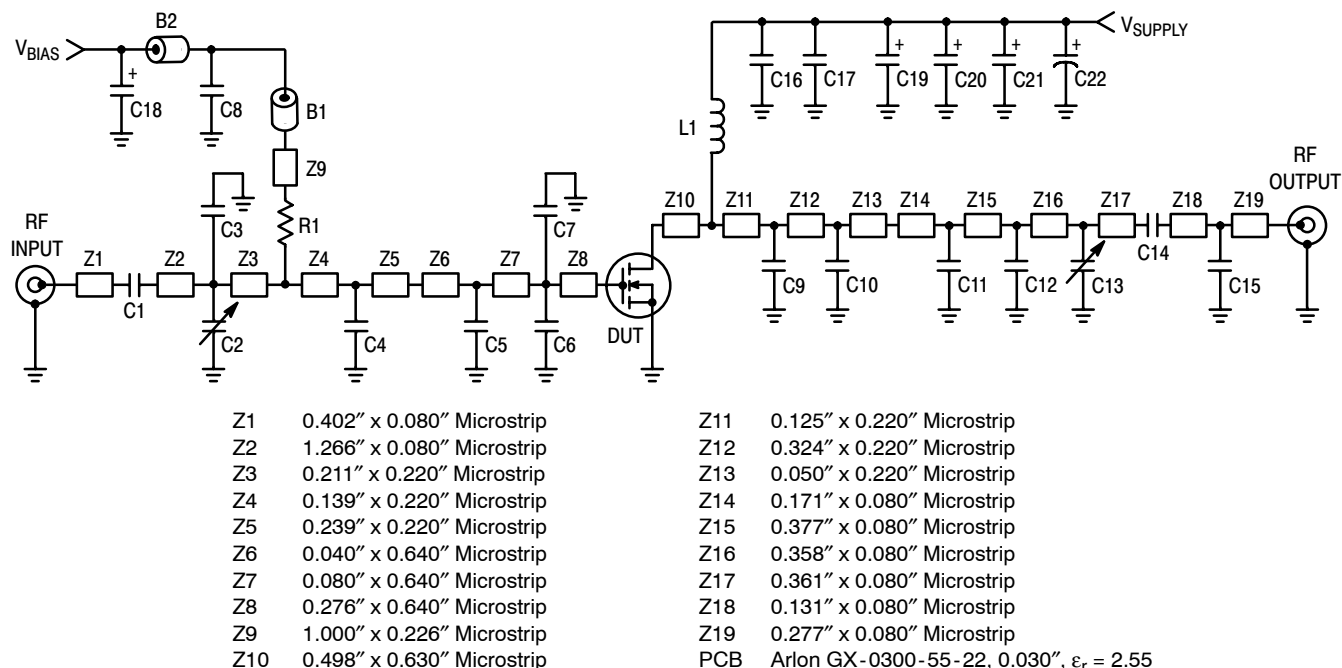


Figure 1. MRF5S4140HR3(SR3) Test Circuit Schematic — 460-470 MHz

Table 5. MRF5S4140HR3(SR3) Test Circuit Component Designations and Values — 460-470 MHz

Part	Description	Part Number	Manufacturer
B1, B2	Ferrite Beads, Short	2743019447	Fair-Rite
C1, C14	120 pF Chip Capacitors	100B121JP500X	ATC
C2, C13	0.8-8.0 pF Variable Capacitors, Gigatrim	27291SL	Johanson
C3	18 pF Chip Capacitor	100B180JP500X	ATC
C4	30 pF Chip Capacitor	100B300JP500X	ATC
C5	24 pF Chip Capacitor	100B240JP500X	ATC
C6, C7	13 pF Chip Capacitors	100B130JP500X	ATC
C8	0.02 μ F, 50 V Chip Capacitor	200B203MW50B	ATC
C9, C10	22 pF Chip Capacitors	100B220JP500X	ATC
C11	1.0 pF Chip Capacitor	100B1R0JP500X	ATC
C12	5.6 pF Chip Capacitor	100B5R6JP500X	ATC
C15	1.5 pF Chip Capacitor	100B1R5JP500X	ATC
C16	47 pF Chip Capacitor	100B47JP500X	ATC
C17	0.56 μ F, 50 V Chip Capacitor	C1825C564J5GAC	Kemet
C18, C19, C20, C21	10 μ F, 35 V Tantalum Chip Capacitors	T491D106K035AS	Kemet
C22	470 μ F, 63 V Electrolytic Capacitor	SME63V471M12X25LL	United Chemi-Con
L1	39 nH Inductor	1812SMS-39N	Coilcraft
R1	100 Ω , 1/4 W Chip Resistor (1210)		

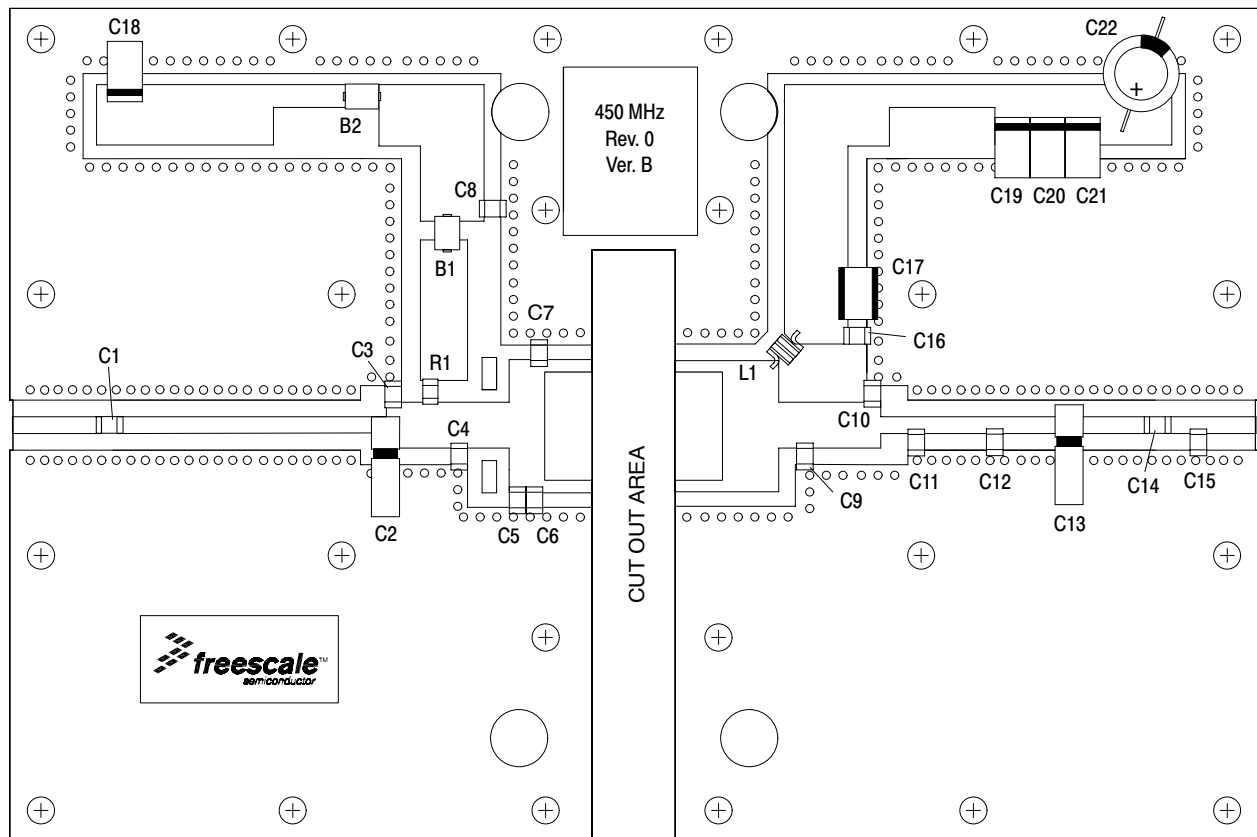
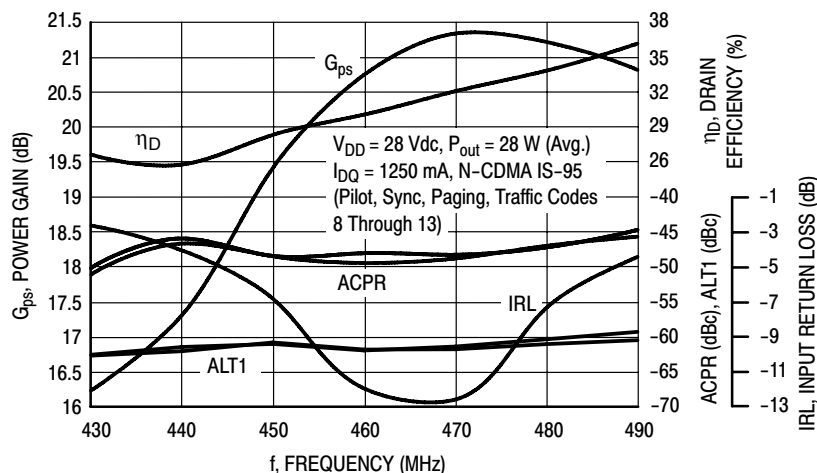
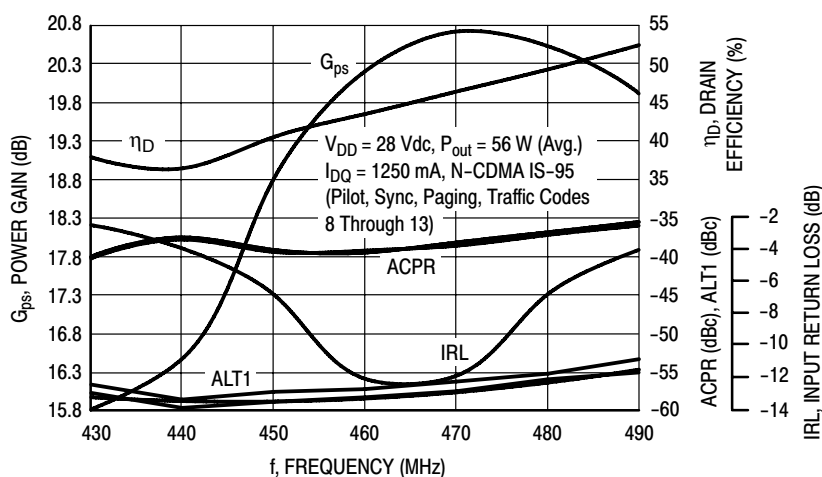


Figure 2. MRF5S4140HR3(SR3) Test Circuit Component Layout — 460-470 MHz

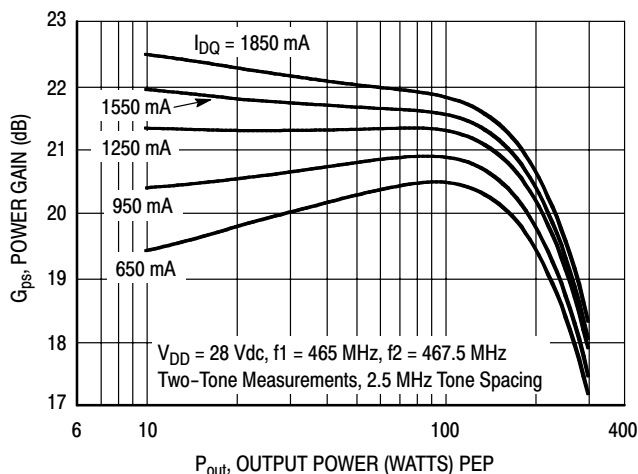
TYPICAL CHARACTERISTICS — 460-470 MHz



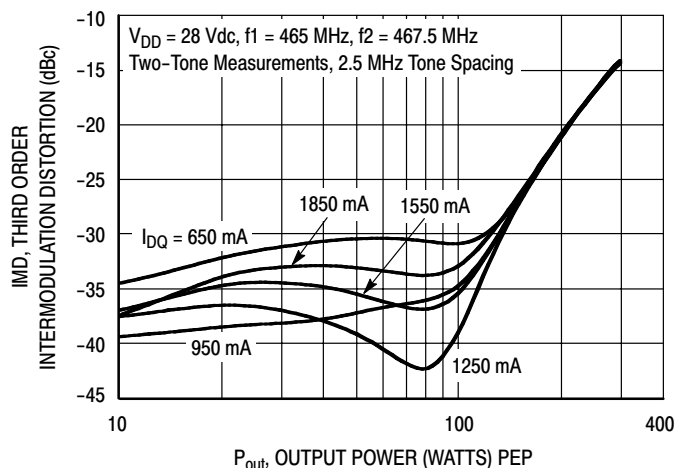
**Figure 3. Single-Carrier N-CDMA Broadband Performance
@ $P_{out} = 28$ Watts Avg.**



**Figure 4. Single-Carrier N-CDMA Broadband Performance
@ $P_{out} = 56$ Watts Avg.**



**Figure 5. Two-Tone Power Gain versus
Output Power**



**Figure 6. Third Order Intermodulation Distortion
versus Output Power**

TYPICAL CHARACTERISTICS — 460-470 MHz

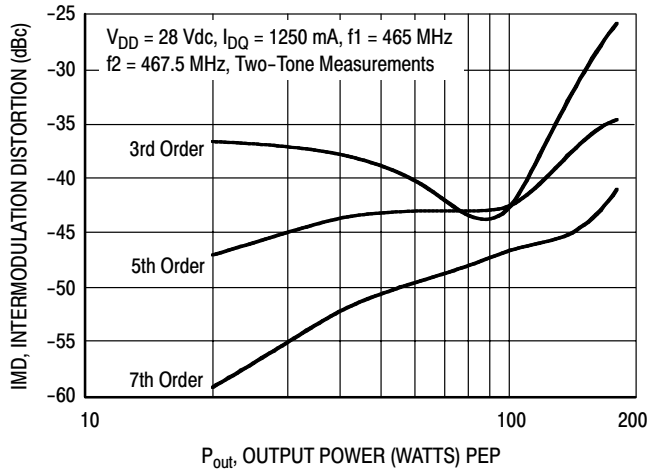


Figure 7. Intermodulation Distortion Products versus Output Power

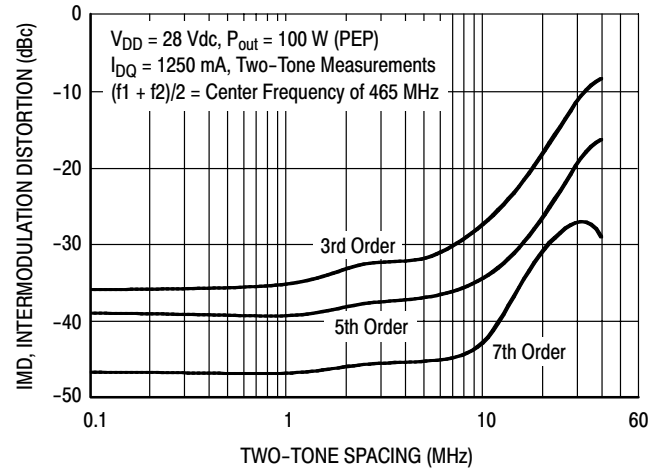


Figure 8. Intermodulation Distortion Products versus Tone Spacing

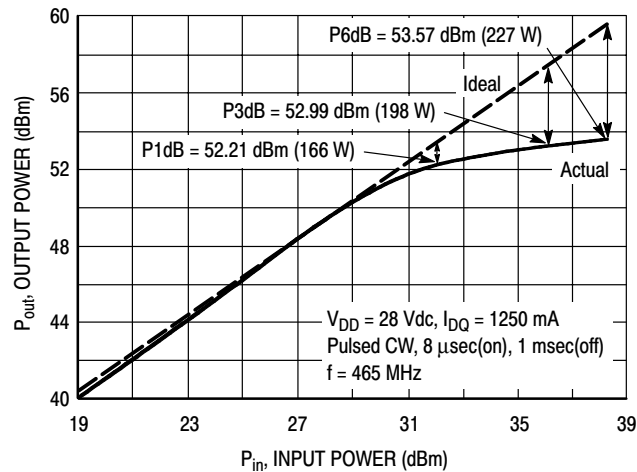


Figure 9. Pulse CW Output Power versus Input Power

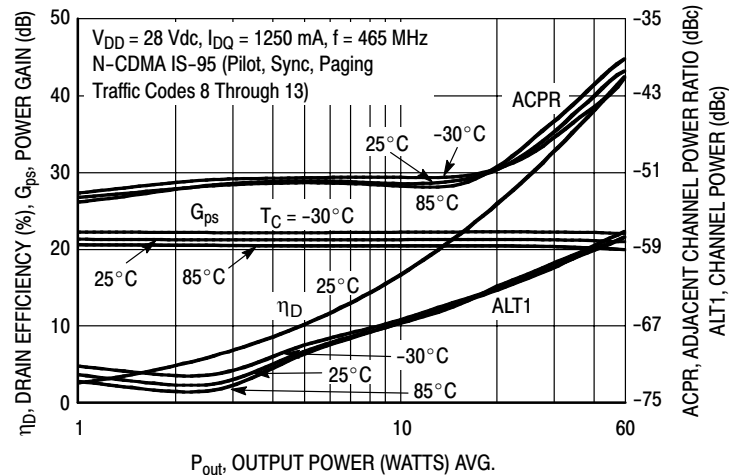


Figure 10. Single-Carrier N-CDMA ACPR, ALT1, Power Gain and Drain Efficiency versus Output Power

TYPICAL CHARACTERISTICS — 460-470 MHz

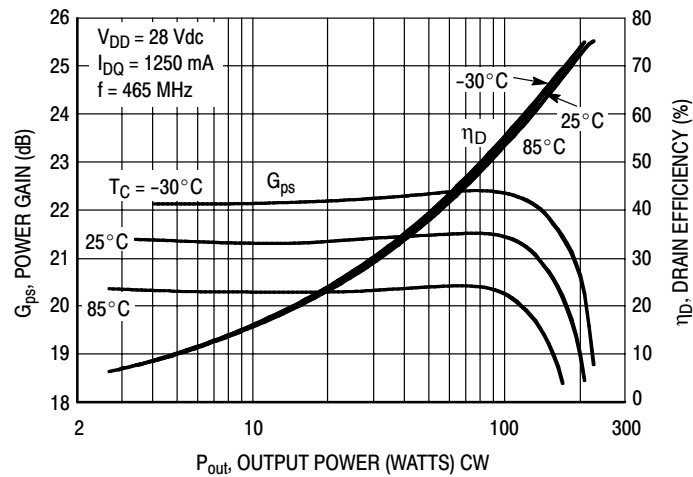


Figure 11. Power Gain and Drain Efficiency versus CW Output Power

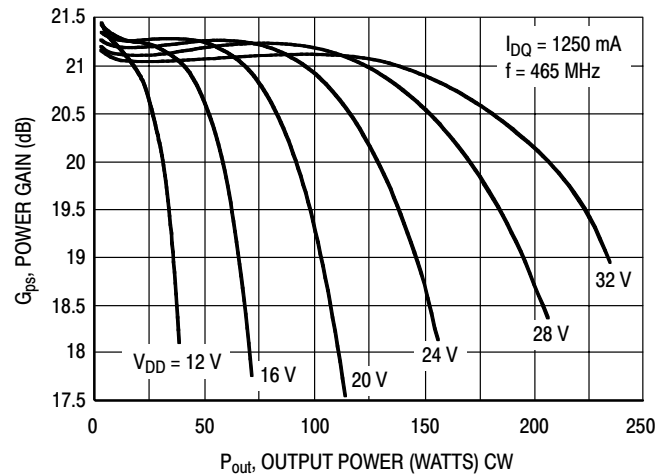
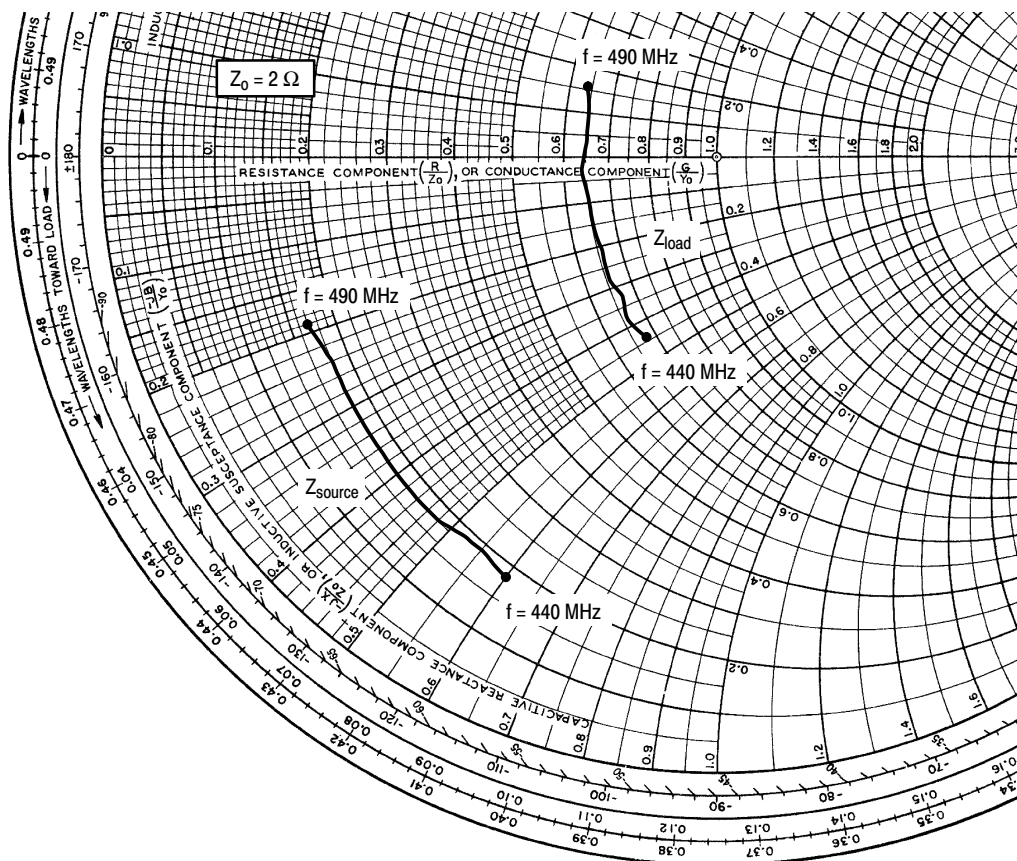


Figure 12. Power Gain versus Output Power



$V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 1250 \text{ mA}$, $P_{out} = 28 \text{ W Avg.}$

f MHz	Z_{source} Ω	Z_{load} Ω
440	$0.359 - j1.19$	$1.35 - j0.870$
445	$0.389 - j1.11$	$1.31 - j0.743$
450	$0.379 - j1.03$	$1.34 - j0.641$
455	$0.360 - j0.959$	$1.32 - j0.539$
460	$0.355 - j0.873$	$1.31 - j0.420$
465	$0.352 - j0.773$	$1.30 - j0.274$
470	$0.350 - j0.710$	$1.29 - j0.173$
475	$0.350 - j0.628$	$1.28 - j0.044$
480	$0.356 - j0.540$	$1.29 + j0.090$
485	$0.355 - j0.473$	$1.29 + j0.195$
490	$0.345 - j0.388$	$1.28 + j0.313$

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

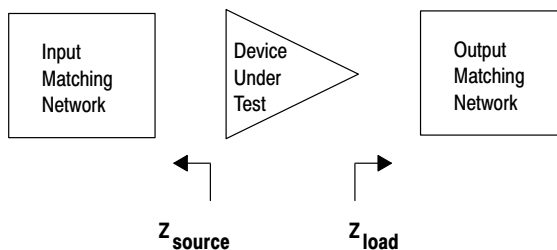


Figure 13. Series Equivalent Source and Load Impedance — 460-470 MHz

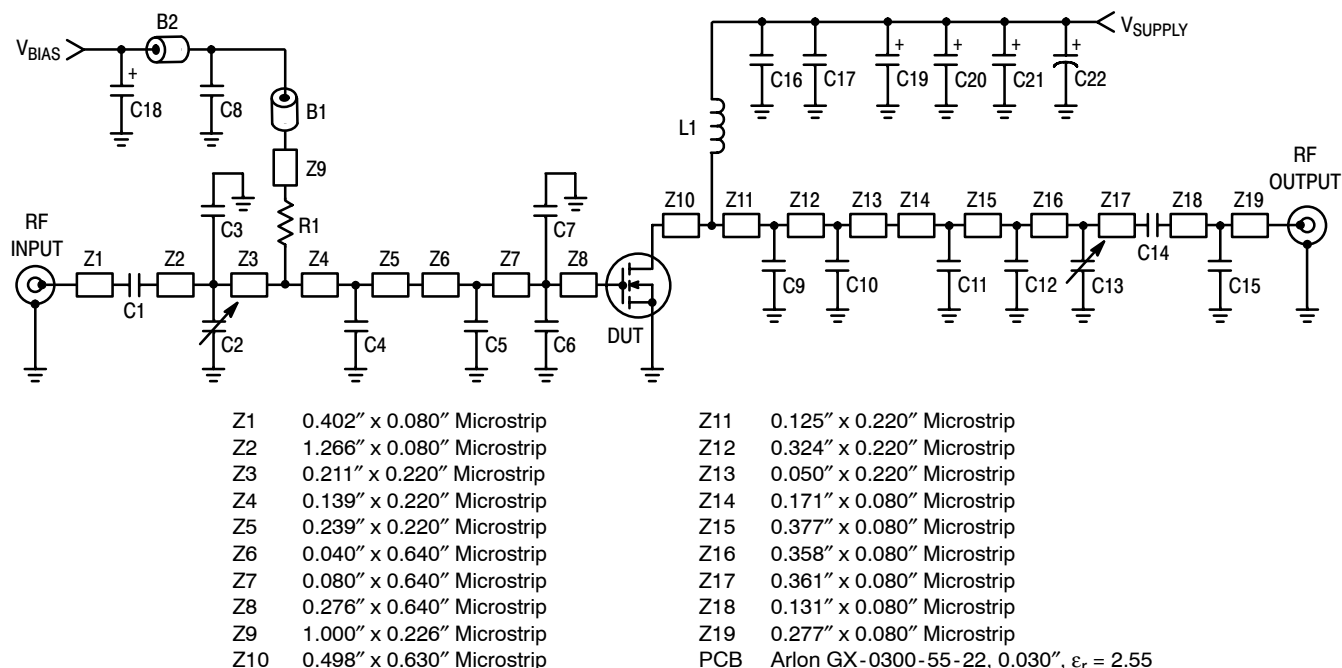


Figure 14. MRF5S4140HR3(SR3) Test Circuit Schematic — 420-430 MHz

Table 6. MRF5S4140HR3(SR3) Test Circuit Component Designations and Values — 420-430 MHz

Part	Description	Part Number	Manufacturer
B1, B2	Ferrite Beads, Short	2743019447	Fair-Rite
C1, C14	120 pF Chip Capacitors	100B121JP500X	ATC
C2, C13	0.8-8.0 pF Variable Capacitors, Gigatrim	27291SL	Johanson
C3	18 pF Chip Capacitor	100B180JP500X	ATC
C4	39 pF Chip Capacitor	100B390JP500X	ATC
C5	24 pF Chip Capacitor	100B240JP500X	ATC
C6, C7	13 pF Chip Capacitors	100B130JP500X	ATC
C8	0.02 μ F, 50 V Chip Capacitor	200B203MW50B	ATC
C9, C10	22 pF Chip Capacitors	100B220JP500X	ATC
C11	1.0 pF Chip Capacitor	100B1R0JP500X	ATC
C12	5.6 pF Chip Capacitor	100B5R6JP500X	ATC
C15	1.5 pF Chip Capacitor	100B1R5JP500X	ATC
C16	47 pF Chip Capacitor	100B47JP500X	ATC
C17	0.56 μ F, 50 V Chip Capacitor	C1825C564J5GAC	Kemet
C18, C19, C20, C21	10 μ F, 35 V Tantalum Chip Capacitors	T491D106K035AS	Kemet
C22	470 μ F, 63 V Electrolytic Capacitor	SME63V471M12X25LL	United Chemi-Con
L1	39 nH Inductor	1812SMS-39N	Coilcraft
R1	100 Ω , 1/4 W Chip Resistor (1210)		

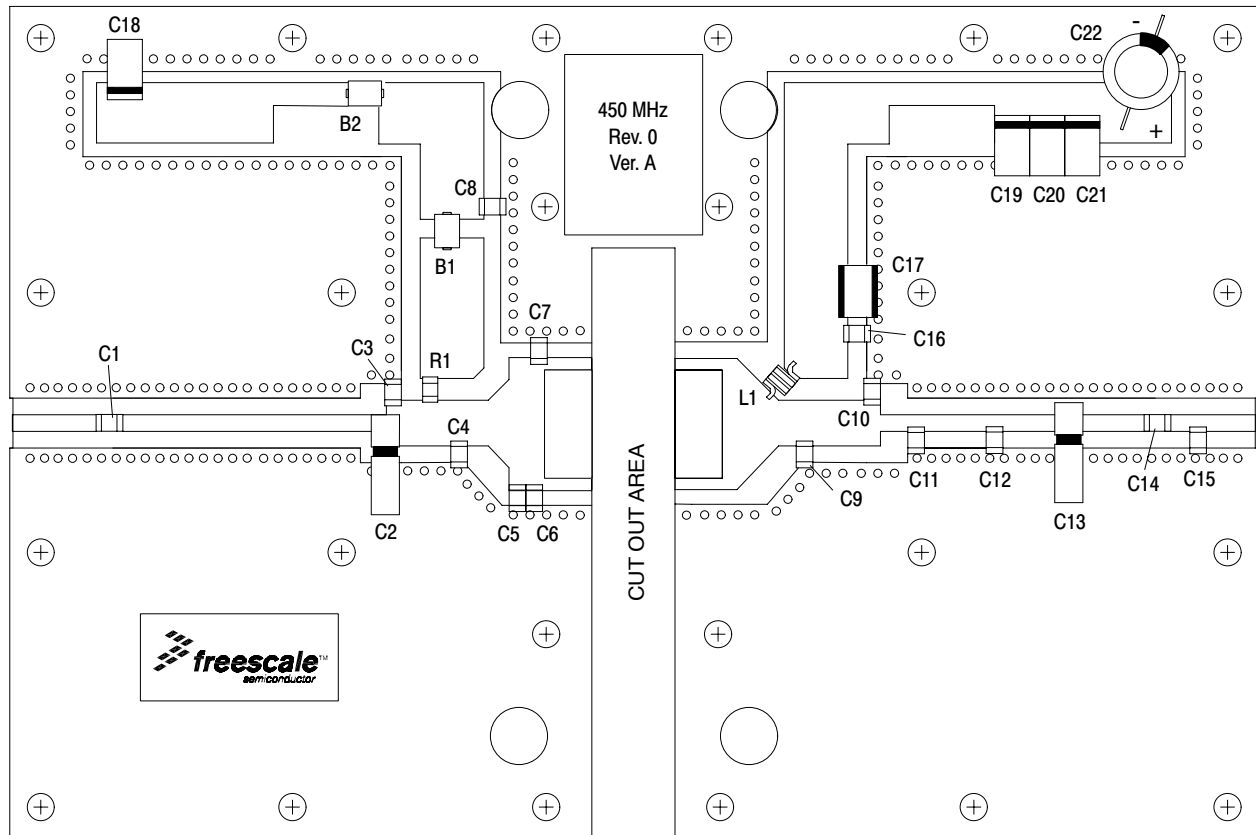
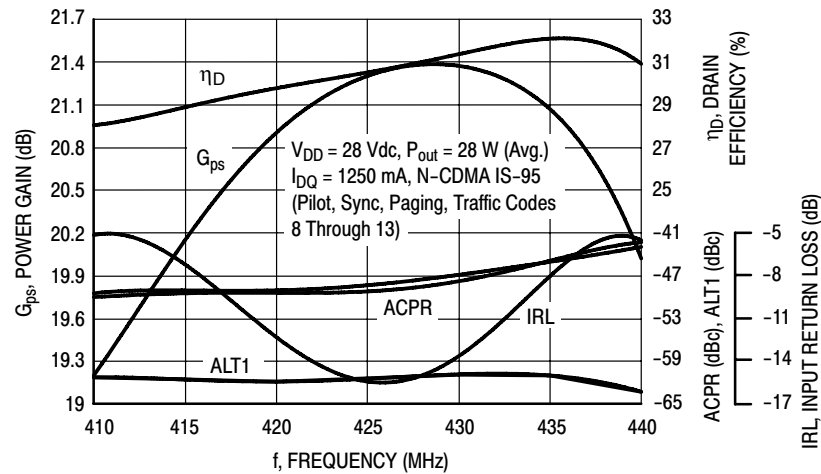
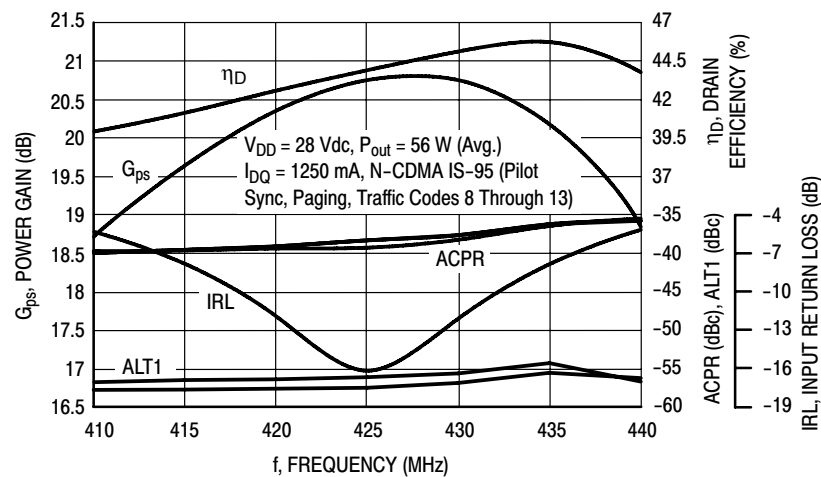


Figure 15. MRF5S4140HR3(SR3) Test Circuit Component Layout — 420-430 MHz

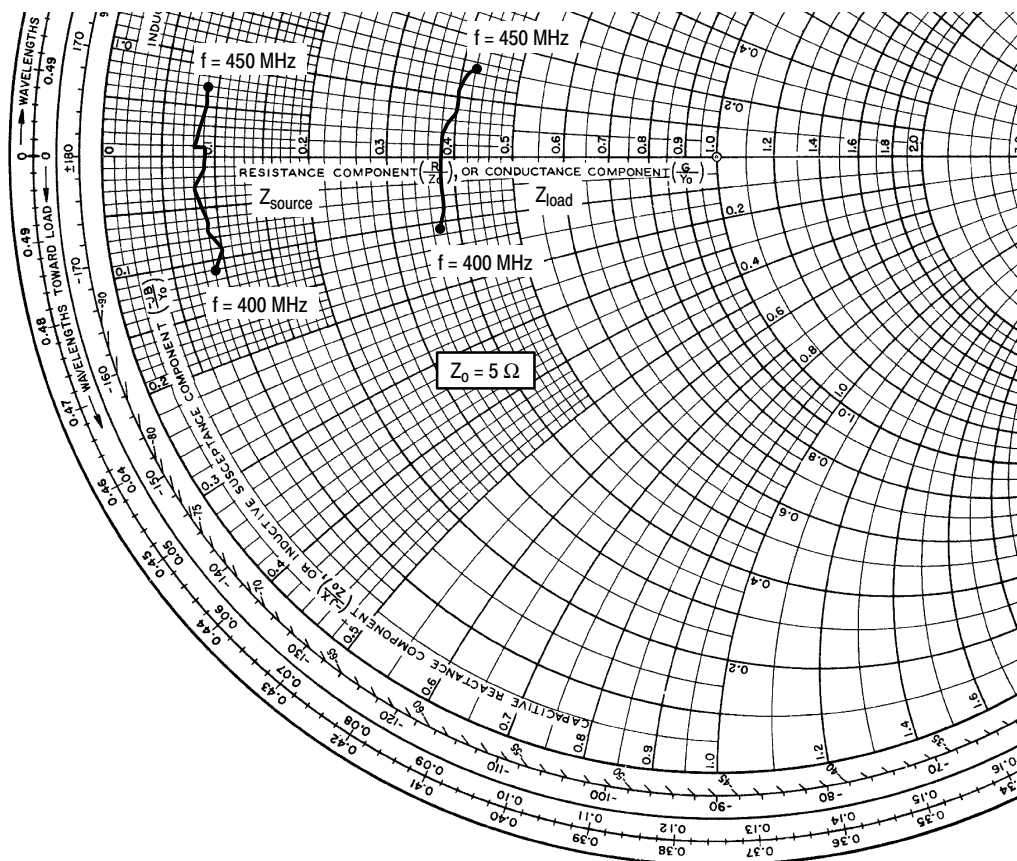
TYPICAL CHARACTERISTICS — 420-430 MHz



**Figure 16. Single-Carrier N-CDMA Broadband Performance
@ $P_{out} = 28$ Watts Avg.**



**Figure 17. Single-Carrier N-CDMA Broadband Performance
@ $P_{out} = 56$ Watts Avg.**



$V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 1250 \text{ mA}$, $P_{out} = 28 \text{ W Avg.}$

f MHz	Z_{source} Ω	Z_{load} Ω
400	$0.454 - j0.530$	$1.87 - j0.530$
405	$0.476 - j0.435$	$1.91 - j0.376$
410	$0.430 - j0.360$	$1.88 - j0.276$
415	$0.455 - j0.281$	$1.91 - j0.046$
420	$0.419 - j0.153$	$1.89 - j0.019$
425	$0.421 - j0.135$	$1.92 + j0.128$
430	$0.435 - j0.032$	$1.97 + j0.276$
435	$0.426 + j0.048$	$1.99 + j0.392$
440	$0.407 + j0.044$	$1.99 + j0.537$
445	$0.429 + j0.262$	$2.05 + j0.675$
450	$0.452 + j0.341$	$2.10 + j0.765$

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

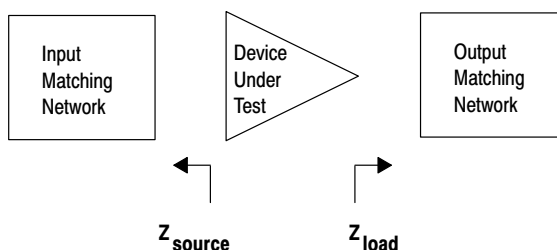
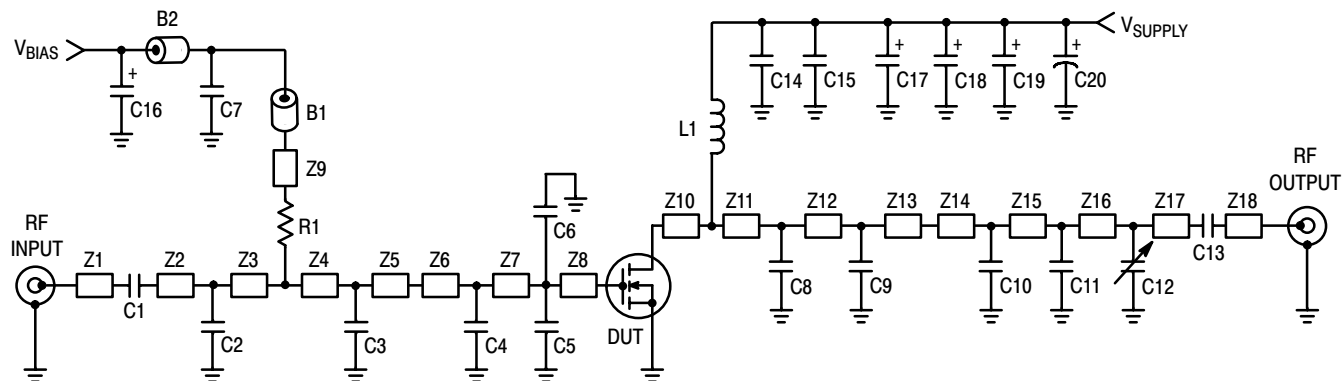


Figure 18. Series Equivalent Source and Load Impedance — 420-430 MHz



Z1	0.402" x 0.080" Microstrip	Z11	0.125" x 0.220" Microstrip
Z2	1.266" x 0.080" Microstrip	Z12	0.324" x 0.220" Microstrip
Z3	0.211" x 0.220" Microstrip	Z13	0.050" x 0.220" Microstrip
Z4	0.139" x 0.220" Microstrip	Z14	0.171" x 0.080" Microstrip
Z5	0.239" x 0.220" Microstrip	Z15	0.377" x 0.080" Microstrip
Z6	0.040" x 0.640" Microstrip	Z16	0.358" x 0.080" Microstrip
Z7	0.080" x 0.640" Microstrip	Z17	0.361" x 0.080" Microstrip
Z8	0.276" x 0.640" Microstrip	Z18	0.408" x 0.080" Microstrip
Z9	1.000" x 0.226" Microstrip	PCB	Arlon GX-0300-55-22, 0.030", $\epsilon_r = 2.55$
Z10	0.498" x 0.630" Microstrip		

Figure 19. MRF5S4140HR3(SR3) Test Circuit Schematic — 489-499 MHz

Table 7. MRF5S4140HR3(SR3) Test Circuit Component Designations and Values — 489-499 MHz

Part	Description	Part Number	Manufacturer
B1, B2	Ferrite Beads, Short	2743019447	Fair-Rite
C1, C13	120 pF Chip Capacitors	100B121JP500X	ATC
C2	18 pF Chip Capacitor	100B180JP500X	ATC
C3, C4	24 pF Chip Capacitors	100B240JP500X	ATC
C5, C6	13 pF Chip Capacitors	100B130JP500X	ATC
C7	0.02 μ F, 50 V Chip Capacitor	200B203MW50B	ATC
C8, C9	22 pF Chip Capacitors	100B220JP500X	ATC
C10	1.0 pF Chip Capacitor	100B1R0JP500X	ATC
C11	5.6 pF Chip Capacitor	100B5R6JP500X	ATC
C12	0.8-8.0 pF Variable Capacitor, Gigatrim	27291SL	Johanson
C14	47 pF Chip Capacitor	100B47JP500X	ATC
C15	0.56 μ F, 50 V Chip Capacitor	C1825C564J5GAC	Kemet
C16, C17, C18, C19	10 μ F, 35 V Tantalum Capacitors	T491D106K035AS	Kemet
C20	470 μ F, 63 V Electrolytic Capacitor	SME63V471M12X25LL	United Chemi-Con
L1	39 nH Inductor	1812SMS-39N	Coilcraft
R1	100 Ω , 1/4 W Chip Resistor (1210)		

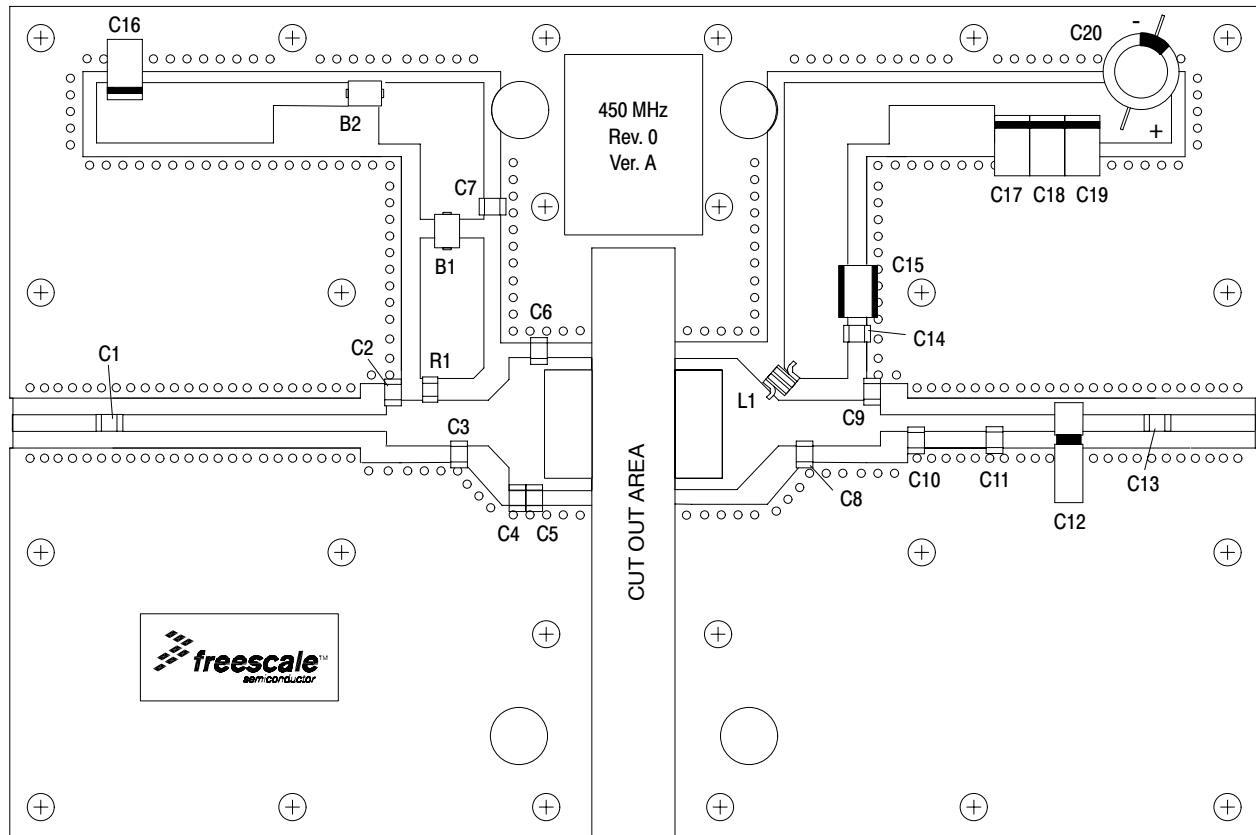
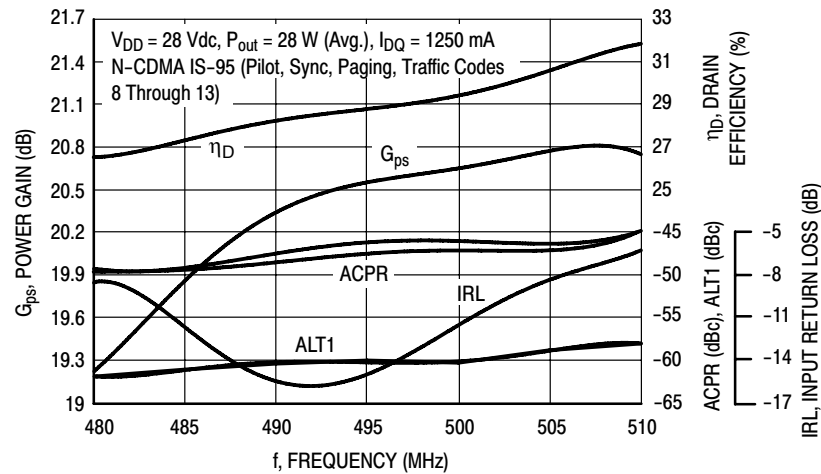
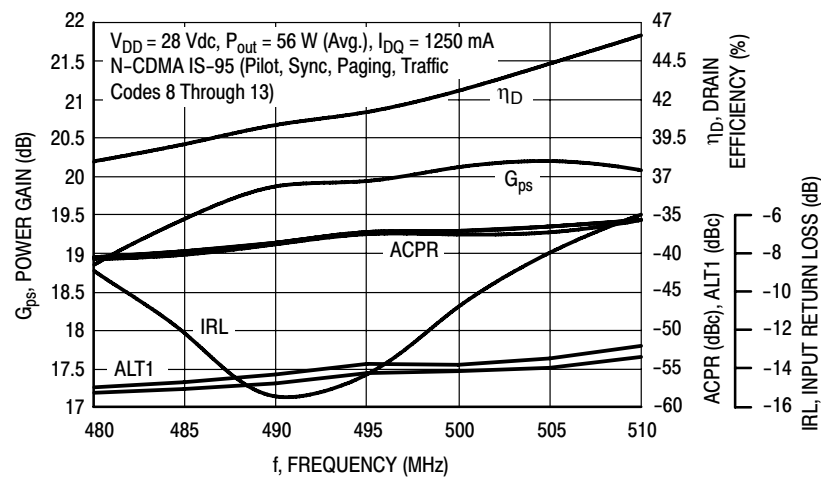


Figure 20. MRF5S4140HR3(SR3) Test Circuit Component Layout — 489-499 MHz

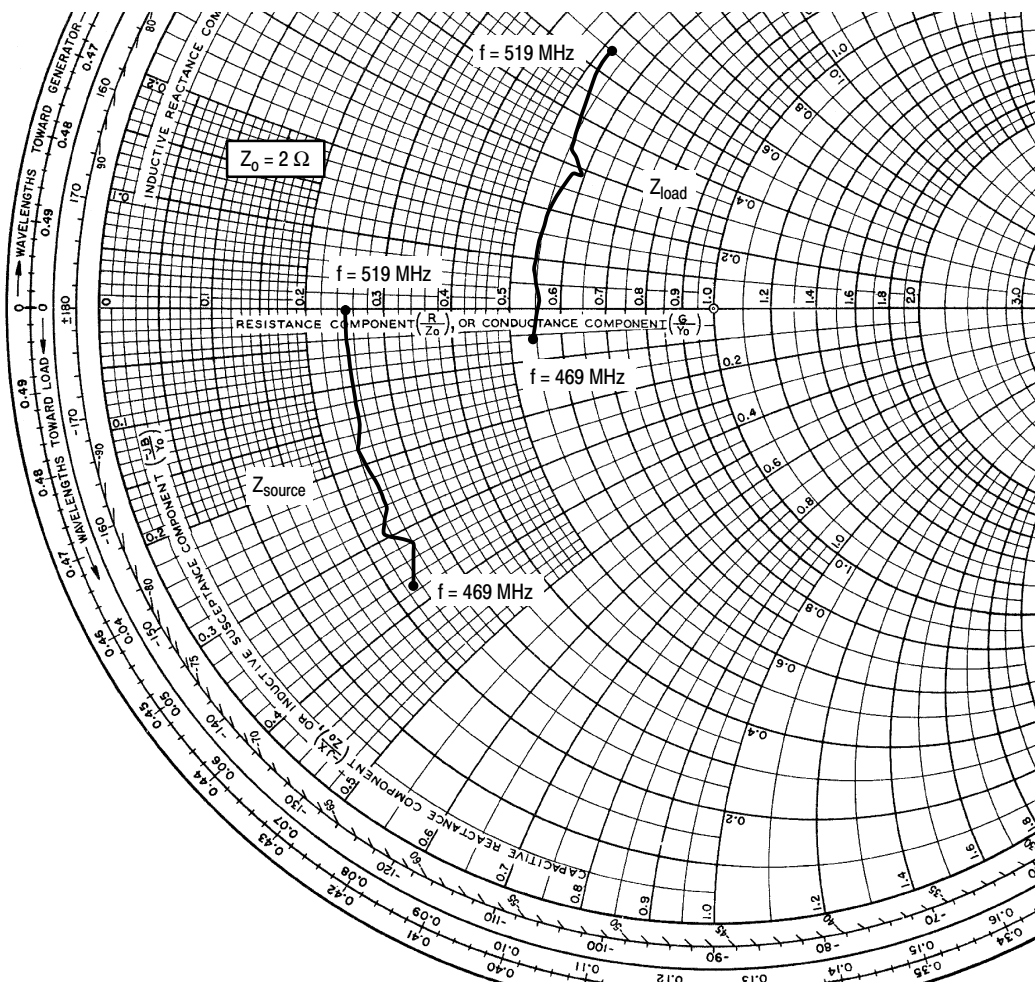
TYPICAL CHARACTERISTICS — 489-499 MHz



**Figure 21. Single-Carrier N-CDMA Broadband Performance
@ $P_{out} = 28$ Watts Avg.**



**Figure 22. Single-Carrier N-CDMA Broadband Performance
@ $P_{out} = 56$ Watts Avg.**



$V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 1250 \text{ mA}$, $P_{out} = 28 \text{ W Avg.}$

f MHz	Z_{source} Ω	Z_{load} Ω
469	$0.454 - j0.742$	$1.08 - j0.129$
474	$0.510 - j0.637$	$1.12 + j0.043$
479	$0.467 - j0.581$	$1.07 + j0.160$
484	$0.495 - j0.513$	$1.09 + j0.294$
489	$0.495 - j0.457$	$1.12 + j0.430$
494	$0.478 - j0.360$	$1.16 + j0.573$
499	$0.505 - j0.295$	$1.18 + j0.586$
504	$0.502 - j0.249$	$1.11 + j0.653$
509	$0.502 - j0.048$	$1.07 + j0.810$
514	$0.499 + j0.002$	$1.03 + j1.01$
519	$0.502 + j0.003$	$1.03 + j1.10$

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

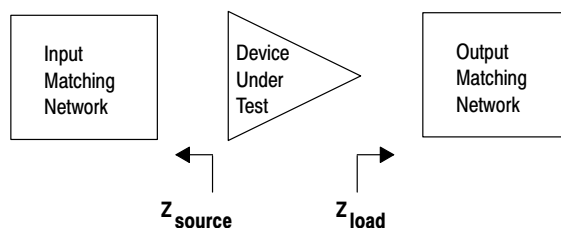
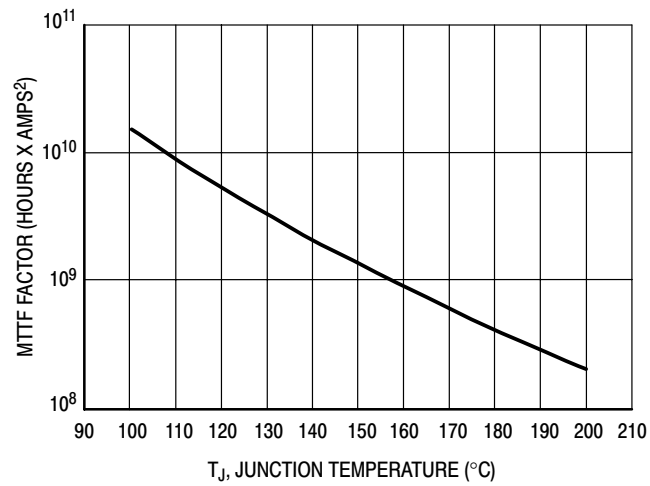


Figure 23. Series Equivalent Source and Load Impedance — 489-499 MHz

TYPICAL CHARACTERISTICS



This above graph displays calculated MTTF in hours x ampere² drain current. Life tests at elevated temperatures have correlated to better than $\pm 10\%$ of the theoretical prediction for metal failure. Divide MTTF factor by I_D^2 for MTTF in a particular application.

Figure 24. MTTF Factor versus Junction Temperature

N-CDMA TEST SIGNAL

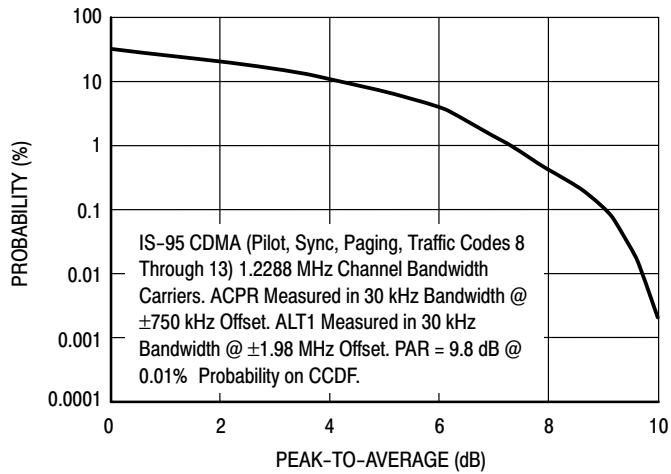


Figure 25. Single-Carrier CCDF N-CDMA

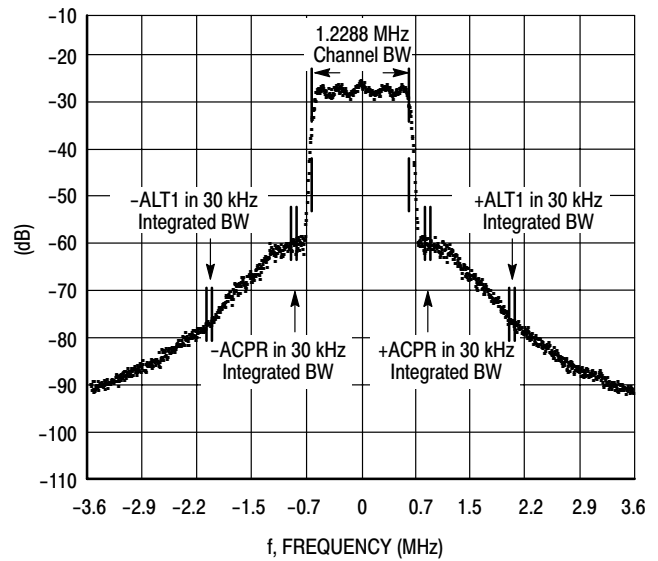
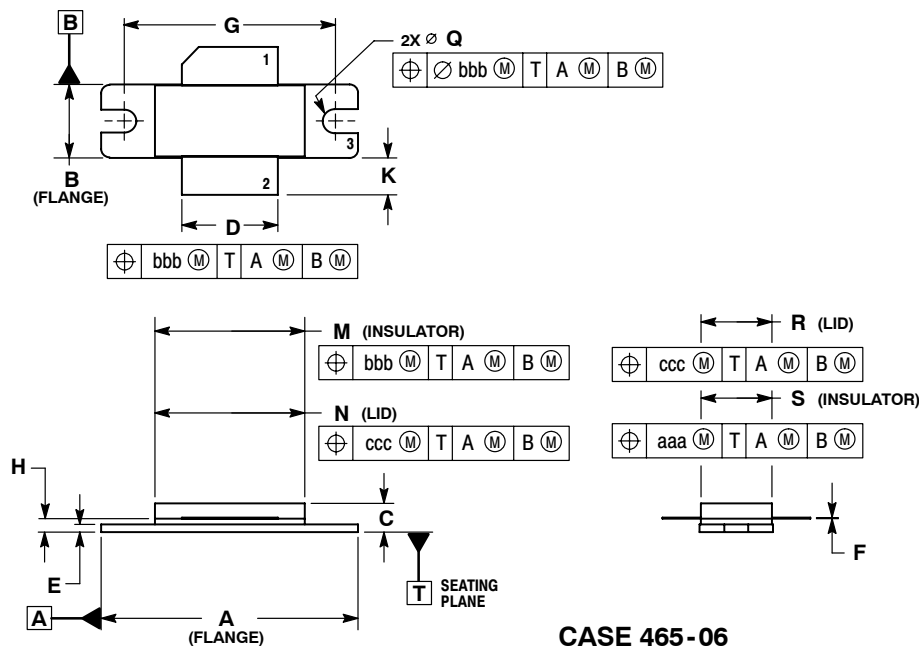


Figure 26. Single-Carrier N-CDMA Spectrum

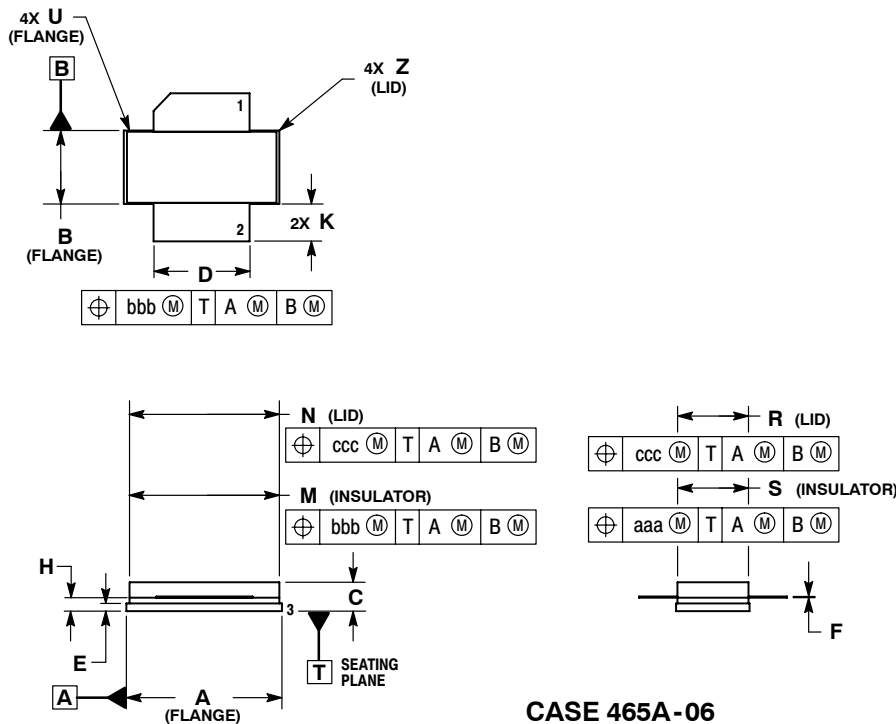
PACKAGE DIMENSIONS



**CASE 465-06
ISSUE G
NI-780
MRF5S4140HR3**

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
G	1.100 BSC		27.94 BSC	
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.66	19.96
N	0.772	0.788	19.60	20.00
Q	$\varnothing$.118	$\varnothing$.138	$\varnothing$ 3.00	$\varnothing$ 3.51
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE



**CASE 465A-06
ISSUE H
NI-780S
MRF5S4140HSR3**

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.805	0.815	20.45	20.70
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.61	20.02
N	0.772	0.788	19.61	20.02
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
U	---	0.040	---	1.02
Z	---	0.030	---	0.76
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
5. SOURCE

MRF5S4140HR3 MRF5S4140HSR3

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